

U.S. UTILITY Patent Application

O.I.P.E.

PATENT DATE

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APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER
09/911581		257	350	2813	Goddie Lee

APPLICANTS
Takahiro OhnakadoTITLE
Si-MOS high-frequency semiconductor device and the manufacturing method of the samePTD-2040
1269

(Primary Examiner)		(Date)	ISSUE DATE NUMBER
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